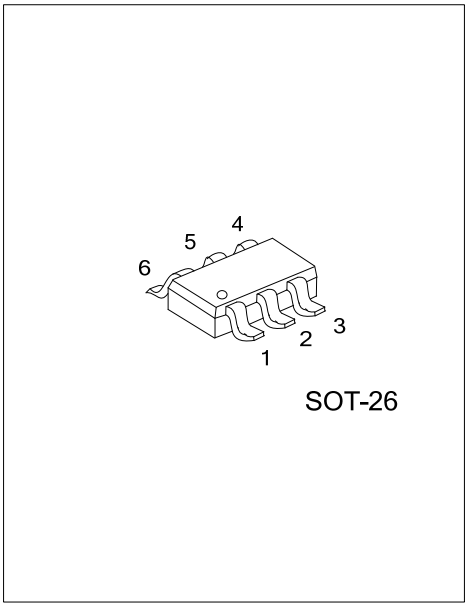
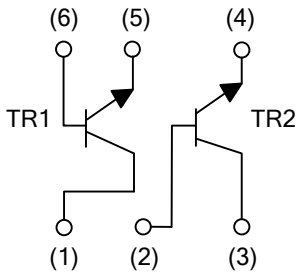
NPN GENERAL PURPOSE DUAL TRANSISTOR



■ FEATURES

* Two independently operating NPN transistors.

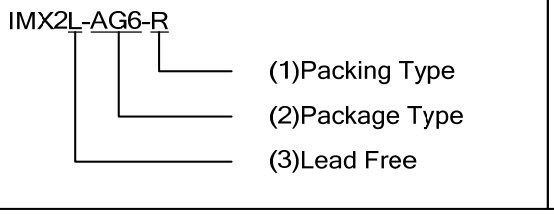
■ EQUIVALENT CIRCUITS



■ ORDERING INFORMATION

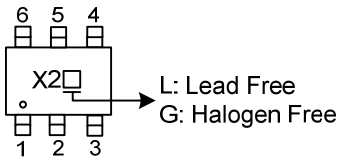
Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
IMX2L-AG6 -R	IMX2G-AG6-R	SOT-26	C1	B2	C2	E2	E1	B1	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter



(1) R: Tape Reel
(2) AG6: SOT-26
(3) G: Halogen Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	150	mA
Collector Power Dissipation	P_C	300 (Note1)	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Note: 1. 200mW per element must not be exceeded.
2. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= 50μA	60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= 1mA	50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= 50μA	7			V
Collector Cut-Off Current	I_{CBO}	V_{CB}= 60V			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}= 7V			0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C / I_B = 50mA/5mA			0.4	V
DC Current Transfer Ratio	h_{FE}	V_{CE}= 6V, I_C= 1mA	120		560	
Transition Frequency (Note)	f_T	V_{CE}=12V, I_E=-2mA, f=100MHz		180		MHz
Output Capacitance	C_{OB}	V_{CB}= 12V, I_E=0A, f=1KHz		2	3.5	pF

Note: Transition frequency of the device.